

IN THE SPECIFICATION:

[0035] Figure 2D shows the result of depositing photoresist 210 over the wafer and patterning it to open an aperture 115 offset from the isolation aperture. The oxide beneath the photoresist can be removed by any convenient process at an appropriate time. The new aperture (and others like it outside the area shown, all referred to as 'field apertures') are located over wide areas of pad nitride and close enough to apertures 110 to facilitate etching the nitride 40 from both sides.